



Product data sheet

1. Product profile

1.1 General description

Planar passivated sensitive gate four quadrant triac in a SOT223 (SC-73) surface-mountable plastic package intended for applications requiring direct interfacing to logic level ICs and low power gate drivers.

1.2 Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drive circuits
- High blocking voltage capability

1.3 Applications

- General purpose low power motor control
- Home appliances

Planar passivated for voltage ruggedness and reliability Sensitive gate in four quadrants

- Surface-mountable package
- Triggering in all four quadrants
- Industrial process control
- Low power AC Fan controllers

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DRM}	repetitive peak off-state voltage		-	-	800	V
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	-	8	A
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	-	1	A



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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	aracteristics					
I _{GT} gate trigger current	0 00	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 9</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see <u>Figure 9</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; see <u>Figure 9</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _i = 25 °C; see <u>Figure 9</u>	-	-	10	mA

 Table 1.
 Quick reference data ...continued

2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1		
2	T2	main terminal 2		T2-T1
3	G	gate		G sym051
4	T2	main terminal 2		
			SOT223 (SOT223)	

3. Ordering information

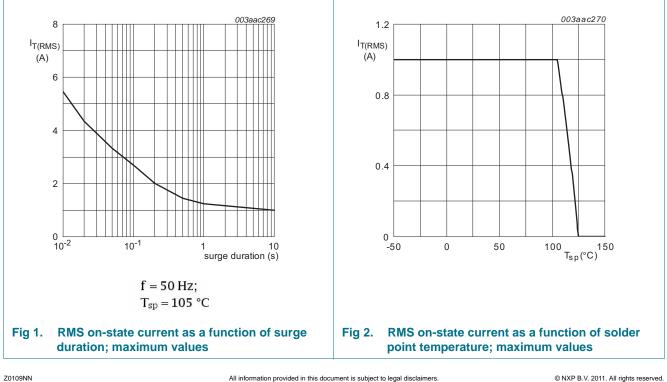
Table 3. Ordering	information		
Type number	Package		
	Name	Description	Version
Z0109NN	SOT223	plastic surface-mounted package with increased heatsink; 4 leads	SOT223

Limiting values 4.

Table 4. **Limiting values**

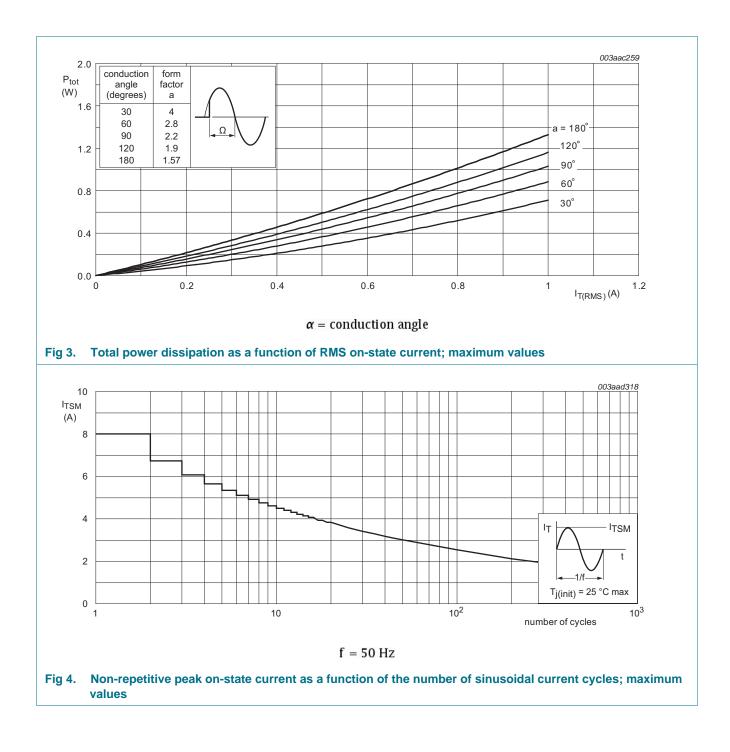
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Мах	Unit
V _{DRM}	repetitive peak off-state voltage		-	800	V
I _{T(RMS)}	RMS on-state current	full sine wave; T _{sp} ≤ 105 °C; see <u>Figure 3</u> ; see <u>Figure 1</u> ; see <u>Figure 2</u>	-	1	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; T _{j(init)} = 25 °C; t _p = 20 ms; see <u>Figure 4</u> ; see <u>Figure 5</u>	-	8	A
		full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 16.7 \text{ ms}$	-	8.5	А
l ² t	l ² t for fusing	t _p = 10 ms; sine-wave pulse	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	I _T = 1 A; I _G = 20 mA; dI _G /dt = 0.1 A/μs; T2+ G+	-	50	A/µs
		I_{T} = 1 A; I_{G} = 20 mA; dI_G/dt = 0.1 A/µs; T2+ G-	-	50	A/µs
		$I_T = 1 \text{ A}; I_G = 20 \text{ mA}; \text{ d}I_G/\text{d}t = 0.1 \text{ A}/\mu\text{s};$ T2- G-	-	50	A/µs
		I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.1 A/µs; T2- G+	-	20	A/µs
I _{GM}	peak gate current		-	1	А
P _{GM}	peak gate power		-	2	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	125	°C



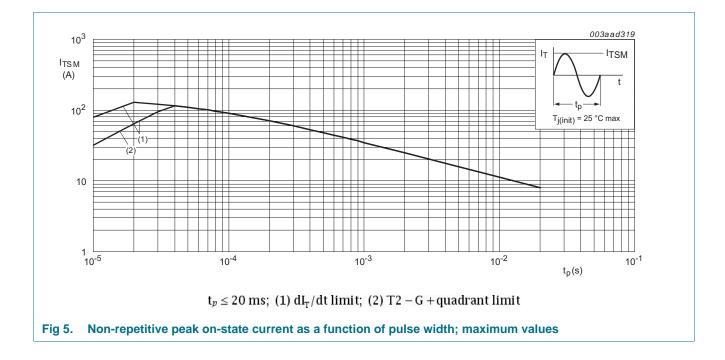
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4Q Triac



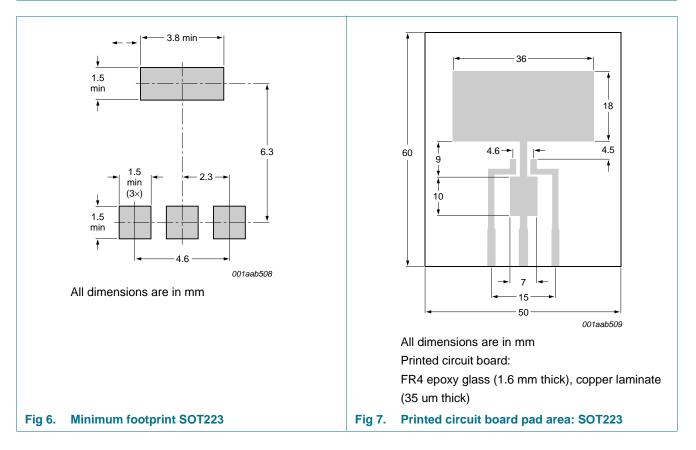
4Q Triac

Z0109NN



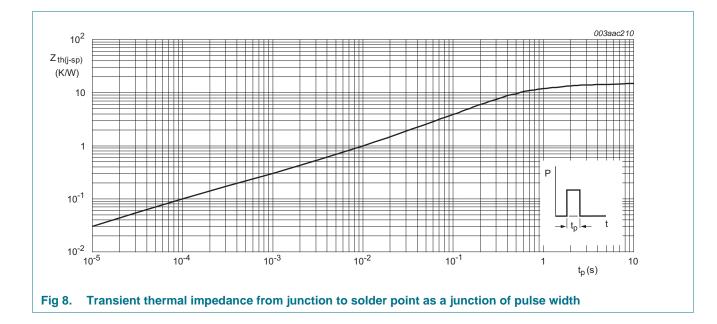
5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; see <u>Figure 8</u>	-	-	15	K/W
R _{th(j-a)}	thermal resistance from junction to	full cycle; printed circuit board mounted; minimum footprint; see <u>Figure 6</u>	-	156	-	K/W
	ambient	full cycle; printed circuit board mounted; pad area; see <u>Figure 7</u>	-	70	-	K/W



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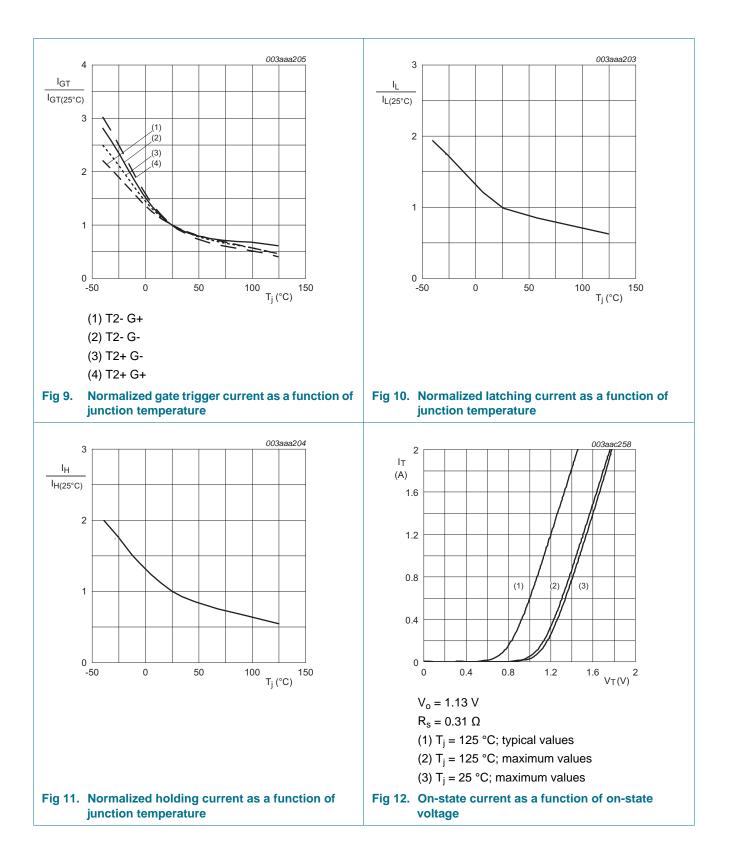


6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; see <u>Figure 9</u>	-	-	10	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; see <u>Figure 9</u>	-	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{100000000000000000000000000000000000$	-	-	10	mA
		$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 9}}{100000000000000000000000000000000000$	-	-	10	mA
ΙL	latching current	$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G+};$ T _j = 25 °C; see <u>Figure 10</u>	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2+ G-};$ T _j = 25 °C; see Figure 10	-	-	25	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G-};$ T _j = 25 °C; see Figure 10	-	-	15	mA
		$V_D = 12 \text{ V}; \text{ I}_G = 0.1 \text{ A}; \text{ T2- G+};$ T _j = 25 °C; see Figure 10	-	-	15	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; see <u>Figure 11</u>	-	-	10	mA
V _T	on-state voltage	I _T = 1.4 A; T _j = 25 °C; see <u>Figure 12</u>	-	1.3	1.6	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 25 \text{ °C};$ see <u>Figure 13</u>	-	-	1.3	V
		$V_D = 800 \text{ V}; \text{ I}_T = 0.1 \text{ A}; \text{ T}_j = 125 \text{ °C};$ see <u>Figure 13</u>	0.2	-	-	V
I _D	off-state current	$V_D = 800 \text{ V}; \text{ T}_j = 125 \text{ °C}$	-	-	0.5	mA
Dynamic o	characteristics					
dV _D /dt	rate of rise of off-state voltage	V _{DM} = 536 V; T _j = 110 °C; gate open circuit; exponential waveform; see <u>Figure 14</u>	50	-	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; \text{ T}_j = 110 \text{ °C};$ $dI_{com}/dt = 0.44 \text{ A/ms}; \text{ gate open circuit}$	2	-	-	V/µs
-						

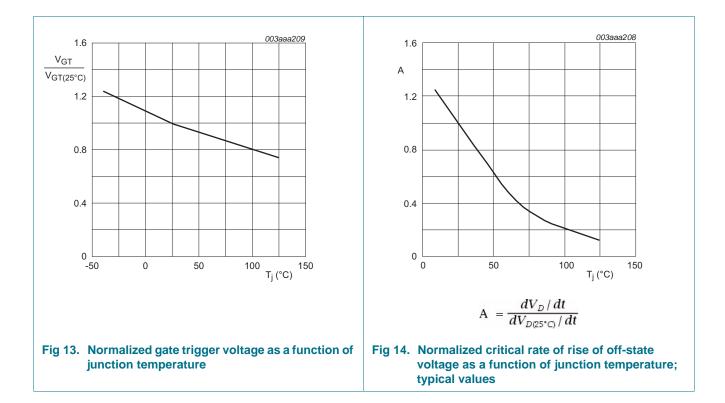
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7. Package outline

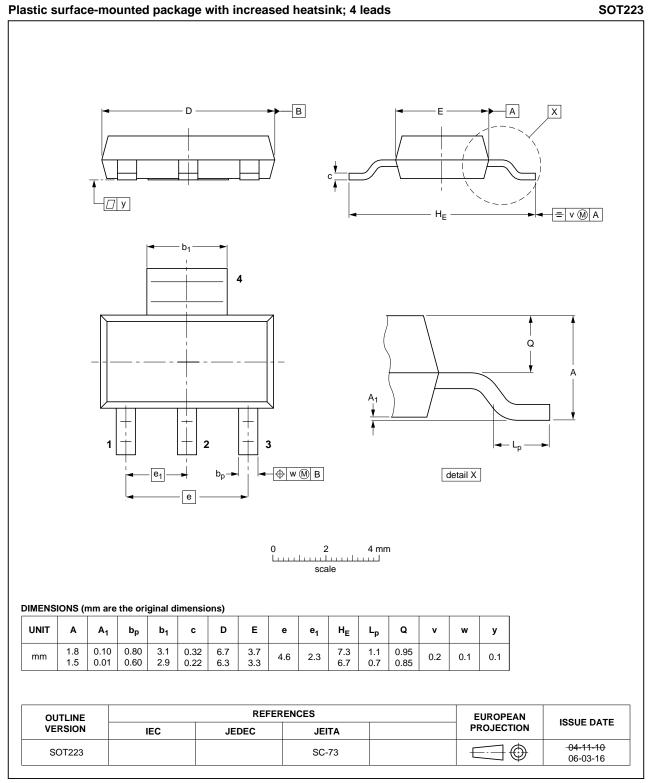


Fig 15. Package outline SOT223 (SOT223)

8. Revision history

Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
Z0109NN v.5	20110318	Product data sheet	-	Z0109NN v.4
Modifications:	 Various chang 	es to content.		
Z0109NN v.4	20100906	Product data sheet	-	Z0109NN v.3

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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